# **Quad 2-Input Exclusive OR Gate**

# **High-Performance Silicon-Gate CMOS**

The MC74HC86A is identical in pinout to the LS86. The device inputs are compatible with standard CMOS outputs; with pullup resistors, they are compatible with LSTTL outputs.

#### **Features**

- Output Drive Capability: 10 LSTTL Loads
- Outputs Directly Interface to CMOS, NMOS, and TTL
- Operating Voltage Range: 2.0 to 6.0 V
- Low Input Current: 1 μA
- High Noise Immunity Characteristic of CMOS Devices
- In Compliance with JEDEC Standard No. 7A Requirements
- Chip Complexity: 56 FETs or 14 Equivalent Gates
- Pb-Free Packages are Available



#### ON Semiconductor®

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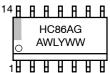
**MARKING DIAGRAMS** 



PDIP-14 **N SUFFIX** CASE 646



SOIC-14 **D SUFFIX** CASE 751A



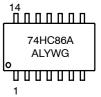


TSSOP-14 **DT SUFFIX** CASE 948G





SOEIAJ-14 **F SUFFIX CASE 965** 



= Assembly Location

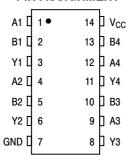
L, WL = Wafer Lot Y. YY = Year W, WW = Work Week G or ■ = Pb-Free Package

(Note: Microdot may be in either location)

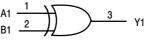
#### **ORDERING INFORMATION**

See detailed ordering and shipping information in the package dimensions section on page 2 of this data sheet.

### PIN ASSIGNMENT

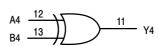


# **LOGIC DIAGRAM**









$$Y = A \oplus B$$
 PIN 14 =  $V_{CC}$   
=  $\overline{A}B + A\overline{B}$  PIN 7 = GND

#### **FUNCTION TABLE**

Inp	Output	
Α	A B	
L	L	L
L	Н	Н
Н	L	Н
Н	Н	L

#### ORDERING INFORMATION

ORDERING INFORMATION	Package	.cn
Device	Packag <mark>e</mark>	Shipping <sup>†</sup>
MC74HC86AN	PDIP-14	
MC74HC86ANG	PDIP-14 (Pb-Free)	25 Units / Rail
MC74HC86AD	SOIC-14	
MC74HC86ADG	SOIC-14 (Pb-Free)	55 Units / Rail
MC74HC86ADR2	SOIC-14	
MC74HC86ADR2G	SOIC-14 (Pb-Free)	2500 / Tape & Reel
MC74HC86ADTR2	TSSOP-14*	·
MC74HC86ADTR2G	TSSOP-14*	
MC74HC86AF	SOEIAJ-14	
MC74HC86AFG	SOEIAJ-14 (Pb-Free)	50 Units / Rail
MC74HC86AFEL	SOEIAJ-14	
MC74HC86AFELG	SOEIAJ-14 (Pb-Free)	2000 / Tape & Reel

<sup>†</sup>For information on tape and reel specifications, including part orientation and tape sizes, please refer to our Tape and Reel Packaging Specifications Brochure, BRD8011/D.

<sup>\*</sup>This package is inherently Pb-Free.

#### **MAXIMUM RATINGS**

Symbol	Parameter	Value	Unit
V <sub>CC</sub>	DC Supply Voltage (Referenced to GND)	- 0.5 to + 7.0	V
V <sub>in</sub>	DC Input Voltage (Referenced to GND)	$-0.5$ to $V_{CC} + 0.5$	V
V <sub>out</sub>	DC Output Voltage (Referenced to GND)	$-0.5$ to $V_{CC} + 0.5$	V
I <sub>in</sub>	DC Input Current, per Pin	±[ <b>2</b> 0	mA
I <sub>out</sub>	DC Output Current, per Pin	± <b>[2</b> 5	mA
I <sub>CC</sub>	DC Supply Current, V <sub>CC</sub> and GND Pins	±[ <b>5</b> 0	mA
P <sub>D</sub>	Power Dissipation in Still Air, Plastic DIP† SOIC Package† TSSOP Package†	750 500 450	mW
T <sub>stg</sub>	Storage Temperature	- 65 to + 150	°C
TL	Lead Temperature, 1 mm from Case for 10 Seconds (Plastic DIP, SOIC or TSSOP Package)	260	°C

This device contains protection circuitry to guard against damage due to high static voltages or electric fields. However, precautions must be taken to avoid applications of any voltage higher than maximum rated voltages to this high-impedance circuit. For proper operation,  $V_{in}$  and  $V_{out}$  should be constrained to the range GND  $\leq$  ( $V_{in}$  or  $V_{out}$ )  $\leq$   $V_{CC}$ .

Unused inputs must always be tied to an appropriate logic voltage level (e.g., either GND or  $V_{CC}$ ). Unused outputs must be left open.

Stresses exceeding Maximum Ratings may damage the device. Maximum Ratings are stress ratings only. Functional operation above the Recommended Operating Conditions is not implied. Extended exposure to stresses above the Recommended Operating Conditions may affect device reliability.

†Derating — Plastic DIP: – 10 mW/ $^{\circ}$ C from 65 $^{\circ}$  to 125 $^{\circ}$ C

SOIC Package: - 7 mW/°C from 65° to 125°C

TSSOP Package: - 6.1 mW/°C from 65° to 125°C

For high frequency or heavy load considerations, see Chapter 2 of the ON Semiconductor High-Speed CMOS Data Book (DL129/D).

#### RECOMMENDED OPERATING CONDITIONS

Symbol	Parameter	Min	Max	Unit
V <sub>CC</sub>	DC Supply Voltage (Referenced to GND)	2.0	6.0	٧
V <sub>in</sub> , V <sub>out</sub>	DC Input Voltage, Output Voltage (Referenced to GND)	0	Vcc	٧
T <sub>A</sub>	Operating Temperature, All Package Types	- 55	+ 125	°C
t <sub>r</sub> , t <sub>f</sub>	Input Rise and Fall Time $V_{CC} = 2.0 \text{ V}$ (Figure 1) $V_{CC} = 4.5 \text{ V}$ $V_{CC} = 6.0 \text{ V}$	0 0 0	1000 500 400	ns

#### DC ELECTRICAL CHARACTERISTICS (Voltages Referenced to GND)

				Gu	aranteed Li	mit	
Symbol	Parameter	Test Conditions	V <sub>CC</sub> V	– 55 to 25°C	≤ <b>85</b> °C	≤ 125°C	Unit
V <sub>IH</sub>	Minimum High-Level Input Voltage	$V_{out} = 0.1 \text{ V or } V_{CC} - 0.1 \text{ V}$ $ I_{out}  \le 20  \mu\text{A}$	2.0 3.0 4.5 6.0	1.5 2.1 3.15 4.2	1.5 2.1 3.15 4.2	1.5 2.1 3.15 4.2	V
V <sub>IL</sub>	Maximum Low-Level Input Voltage	$V_{out} = 0.1 \text{ V or } V_{CC} - 0.1 \text{ V}$ $ I_{out}  \le 20  \mu\text{A}$	2.0 3.0 4.5 6.0	0.5 0.9 1.35 1.8	0.5 0.9 1.35 1.8	0.5 0.9 1.35 1.8	V
V <sub>OH</sub>	Minimum High-Level Output Voltage	$V_{in} = V_{IH} \text{ or } V_{IL}$ $ I_{out}  \le 20 \ \mu\text{A}$	2.0 4.5 6.0	1.9 4.4 5.9	1.9 4.4 5.9	1.9 4.4 5.9	V
		$\begin{split} V_{\text{in}} = V_{\text{IH}} \text{ or } V_{\text{IL}} &  \left I_{\text{out}}\right  \leq 2.4 \text{ mA} \\ \left I_{\text{out}}\right  \leq 4.0 \text{ mA} \\ \left I_{\text{out}}\right  \leq 5.2 \text{ mA} \end{split}$	3.0 4.5 6.0	2.48 3.98 5.48	2.34 3.84 5.34	2.20 3.70 5.20	
V <sub>OL</sub>	Maximum Low-Level Output Voltage	$V_{in} = V_{IH} \text{ or } V_{IL}$ $ I_{out}  \le 20 \ \mu\text{A}$	2.0 4.5 6.0	0.1 0.1 0.1	0.1 0.1 0.1	0.1 0.1 0.1	V
		$ \begin{aligned} V_{\text{in}} = V_{\text{IH}} \text{ or } V_{\text{IL}} & & \left  I_{\text{out}} \right  \leq 2.4 \text{ mA} \\ & \left  I_{\text{out}} \right  \leq 4.0 \text{ mA} \\ & \left  I_{\text{out}} \right  \leq 5.2 \text{ mA} \end{aligned} $	3.0 4.5 6.0	0.26 0.26 0.26	0.33 0.33 0.33	0.40 0.40 0.40	

### DC ELECTRICAL CHARACTERISTICS (Voltages Referenced to GND)

				Gu	aranteed Li	mit	
Symbol	Parameter	Test Conditions	V <sub>CC</sub> V	– 55 to 25°C	≤ <b>85</b> °C	≤ 125°C	Unit
I <sub>in</sub>	Maximum Input Leakage Current	V <sub>in</sub> = V <sub>CC</sub> or GND	6.0	±[0.1	±[1.0	±[1.0	μΑ
Icc	Maximum Quiescent Supply Current (per Package)	$V_{in} = V_{CC}$ or GND $I_{out} = 0 \mu A$	6.0	1.0	10	40	μΑ

NOTE: Information on typical parametric values can be found in Chapter 2 of the ON Semiconductor High-Speed CMOS Data Book (DL129/D).

### AC ELECTRICAL CHARACTERISTICS ( $C_L$ = 50 pF, Input t, = $t_f$ = 6 ns)

			Guaranteed Limit				
Symbol	Parameter	V <sub>CC</sub>	– 55 to 25°C	≤ 85°C	≤ 125°C	Unit	
t <sub>PLH</sub> , t <sub>PHL</sub>	Maximum Propagation Delay, Input A or B to Output Y (Figures 1 and 2)	2.0 3.0 4.5 6.0	100 80 20 17	125 90 25 21	150 110 31 26	ns	
t <sub>TLH</sub> , t <sub>THL</sub>	Maximum Output Transition Time, Any Output (Figures 1 and 2)	2.0 3.0 4.5 6.0	75 30 15 13	95 40 19 16	110 55 22 19	ns	
C <sub>in</sub>	Maximum Input Capacitance	0c 30	10	10	10	pF	

#### NOTES:

- 1. For propagation delays with loads other than 50 pF, see Chapter 2 of the ON Semiconductor High-Speed CMOS Data Book (DL129/D).
- 2. Information on typical parametric values can be found in Chapter 2 of the ON Semiconductor High-Speed CMOS Data Book (DL129/D).

			Typical @ 25°C, V <sub>CC</sub> = 5.0 V	
$C_{PD}$	Power Dissipation Capacitance (Per Gate)*		33	pF

<sup>\*</sup>Used to determine the no-load dynamic power consumption: P<sub>D</sub> = C<sub>PD</sub> V<sub>CC</sub><sup>2</sup>f + I<sub>CC</sub> V<sub>CC</sub>. For load considerations, see Chapter 2 of the ON Semiconductor High-Speed CMOS Data Book (DL129/D).

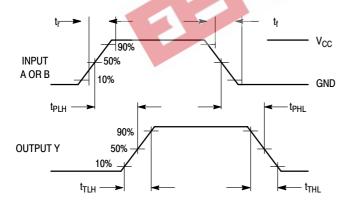
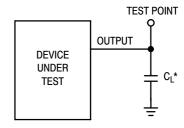


Figure 1. Switching Waveforms



\*Includes all probe and jig capacitance

Figure 2. Test Circuit

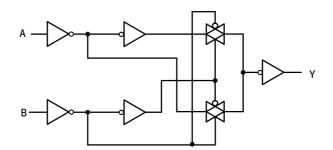
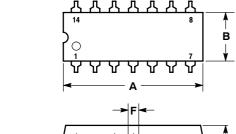
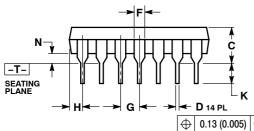


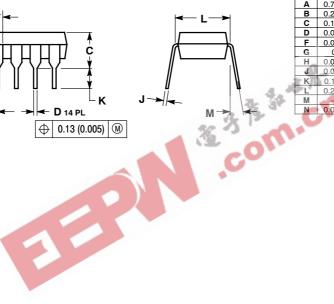
Figure 3. Expanded Logic Diagram (1/4 of Device)

#### **PACKAGE DIMENSIONS**

PDIP-14 CASE 646-06 ISSUE P





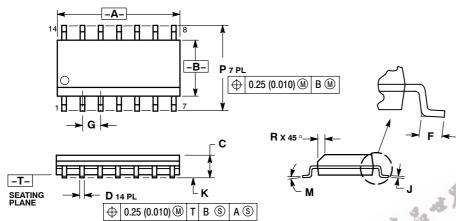


- NOTES:
  1. DIMENSIONING AND TOLERANCING PER ANSI Y14.5M, 1982.
  2. CONTROLLING DIMENSION: INCH.
  3. DIMENSION L TO CENTER OF LEADS WHEN FORMED PARALLEL.
  4. DIMENSION B DOES NOT INCLUDE MOLD FLASH.
  5. ROUNDED CORNERS OPTIONAL.

	INC	HES MILLIMETE		IETERS
DIM	MIN	MAX	MIN	MAX
Α	0.715	0.770	18.16	19.56
В	0.240	0.260	6.10	6.60
С	0.145	0.185	3.69	4.69
D	0.015	0.021	0.38	0.53
F	0.040	0.070	1.02	1.78
G	0.100	BSC	2.54	BSC
H	0.052	0.095	1.32	2.41
d	0.008	0.015	0.20	0.38
K	0.115	0.135	2.92	3.43
P.L	0.290	0.310	7.37	7.87
M	-	10 °		10 °
N	0.015	0.039	0.38	1.01

#### **PACKAGE DIMENSIONS**

SOIC-14 CASE 751A-03 **ISSUE H** 

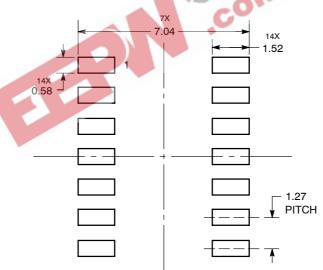


- NOTES:
  1. DIMENSIONING AND TOLERANCING PER

- I. DIMENSIONING AND TOLERANCING PER ANSI Y14.5M, 1982.
   CONTROLLING DIMENSION: MILLIMETER.
   DIMENSIONS A AND B DO NOT INCLUDE MOLD PROTRUSION.
   MAXIMUM MOLD PROTRUSION 0.15 (0.006) PER SIDE.
   DIMENSION D DOES NOT INCLUDE DAMBAR PROTRUSION. ALLOWABLE DAMBAR PROTRUSION SHALL BE 0.127 (0.005) TOTAL IN EXCESS OF THE D DIMENSION AT MAXIMUM MATERIAL CONDITION.

	MILLIMETERS		INC	HES
DIM	MIN	MAX	MIN	MAX
Α	8.55	8.75	0.337	0.344
В	3.80	4.00	0.150	0.157
C	1.35	1.75	0.054	0.068
ם	0.35	0.49	0.014	0.019
F	0.40	1.25	0.016	0.049
G	1.27 BSC		0.050	BSC
J	0.19	0.25	0.008	0.009
_K	0.10	0.25	0.004	0.009
M	0 °	7°	0 °	7°
P	5.80	6.20	0.228	0.244
R	0.25	0.50	0.010	0.019

### SOLDERING FOOTPRINT

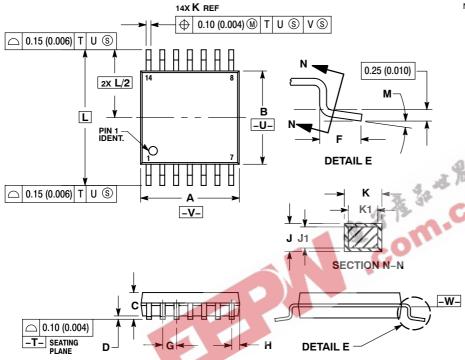


DIMENSIONS: MILLIMETERS

<sup>\*</sup>For additional information on our Pb-Free strategy and soldering details, please download the ON Semiconductor Soldering and Mounting Techniques Reference Manual, SOLDERRM/D.

#### PACKAGE DIMENSIONS

TSSOP-14 CASE 948G-01 **ISSUE B** 



- NOTES:

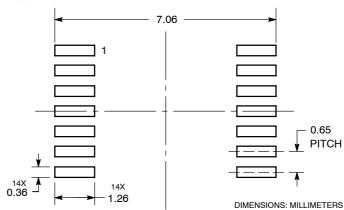
  1. DIMENSIONING AND TOLERANCING PER ANSI Y14.5M, 1982.
  2. CONTROLLING DIMENSION: MILLIMETER.
  3. DIMENSION A DOES NOT INCLUDE MOLD FLASH, PROTRUSIONS OR GATE BURRS. MOLD FLASH OR GATE BURRS SHALL NOT EXCEED 0.15 (0.006) PER SIDE.
  4. DIMENSION B DOES NOT INCLUDE INTERLEAD FLASH OR PROTRUSION. INTERLEAD FLASH OR PROTRUSION SHALL NOT EXCEED 0.25 (0.010) PER SIDE.
  - INTERLEAD FLASH OR PROTRUSION SHAL NOT EXCEED 0.25 (0.010) PER SIDE.

    5. DIMENSION K DOES NOT INCLUDE DAMBAR PROTRUSION. ALLOWABLE DAMBAR PROTRUSION SHALL BE 0.08 (0.003) TOTAL IN EXCESS OF THE K DIMENSION AT MAXIMUM MATERIAL CONDITION.

    6. TERMINAL NUMBERS ARE SHOWN FOR DEEEDEBLE ONLY.
  - REFERENCE ONLY.
    7. DIMENSION A AND B ARE TO BE

DETE		AT DA		ANE -W HES
DIM	MIN	MAX	MIN	MAX
Α	4.90	5.10	0.193	0.200
В	4.30	4.50	0.169	0.177
С		1.20		0.047
D	0.05	0.15	0.002	0.006
F	0.50	0.75	0.020	0.030
G	0.65	BSC	0.026	BSC
Н	0.50	0.60	0.020	0.024
J	0.09	0.20	0.004	0.008
J1	0.09	0.16	0.004	0.006
K	0.19	0.30	0.007	0.012
K1	0.19	0.25	0.007	0.010
L	6.40	6.40 BSC 0.252 BS0		BSC
М	0 °	8 °	0°	8 °

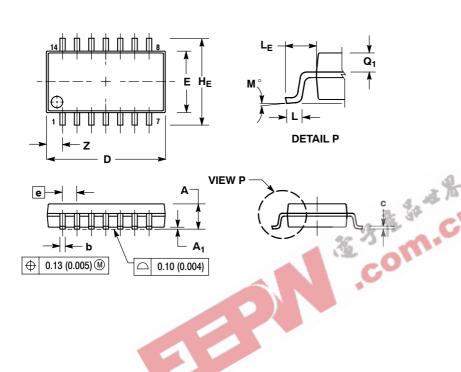
#### **SOLDERING FOOTPRINT\***



\*For additional information on our Pb-Free strategy and soldering details, please download the ON Semiconductor Soldering and Mounting Techniques Reference Manual, SOLDERRM/D.

#### PACKAGE DIMENSIONS

SOEIAJ-14 CASE 965-01 ISSUE A



#### NOTES:

- DIMENSIONING AND TOLERANCING PER ANSI
- CONTROLLING DIMENSION: MILLIMETER.
- DIMENSIONS D AND E DO NOT INCLUDE MOLD FLASH OR PROTRUSIONS AND ARE MEASURED AT THE PARTING LINE. MOLD FLASH OR PROTRUSIONS SHALL NOT EXCEED 0.15 (0.006) PER SIDE.
- (0.006) PER SIDE.

  . TERMINIAL NUMBERS ARE SHOWN FOR REFERENCE ONLY.

  . THE LEAD WIDTH DIMENSION (b) DOES NOT INCLUDE DAMBAR PROTRUSION ALLOWABLE DAMBAR PROTRUSION SHALL BE 0.08 (0.003) TOTAL IN EXCESS OF THE LEAD WIDTH
  DIMENSION AT MAXIMUM MATERIAL CONDITION. DAMBAR CANNOT BE LOCATED ON THE LOWER RADIUS OR THE FOOT. MINIMUM SPACE BETWEEN PROTRUSIONS AND ADJACENT LEAD TO BE 0.46 ( 0.018).

	MILLIMETERS		INC	HES
DIM	MIN	MAX	MIN	MAX
Α		2.05		0.081
A <sub>1</sub>	0.05	0.20	0.002	0.008
b	0.35	0.50	0.014	0.020
С	0.10	0.20	0.004	0.008
D	9.90	10.50	0.390	0.413
Е	5.10	5.45	0.201	0.215
е	1.27	BSC	0.050	BSC
HE	7.40	8.20	0.291	0.323
0.50	0.50	0.85	0.020	0.033
LE	1.10	1.50	0.043	0.059
M	0 °	10°	0 °	10°
$Q_1$	0.70	0.90	0.028	0.035
Z		1.42		0.056

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